



DV SERIES

6 to 10kV, 55 to 75mA, 75nS
Axial Lead Low Current Diodes



Features

- Subminiature Package
- Molded Plastic Body, ANSI/UL94 V-0 Rated Material

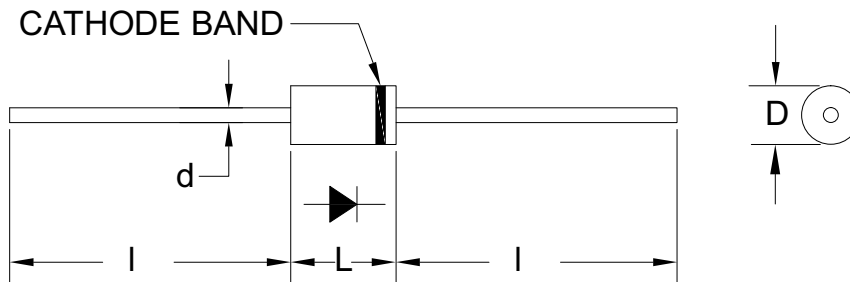
Specifications¹

Part Number	V _{RRM} V	I _{FAVM} mA	V _F V	I _R μA	I _{FSM} A	C _J pF	T _{RR} nS	L in.	D in.	d in.	l in.
DV6P	6000	75	8.0	0.02	3	1.30	75	0.195	0.08	0.02	1.0
DV8P	8000	60	11.5	0.02	3	0.90	75	0.195	0.08	0.02	1.0
DV10P	10000	55	16.0	0.04	3	0.65	75	0.195	0.08	0.02	1.0

Temperature °C	
Operating Temperature	-55 to 150
Storage Temperature	-55 to 175
Maximum Junction Temperature	150

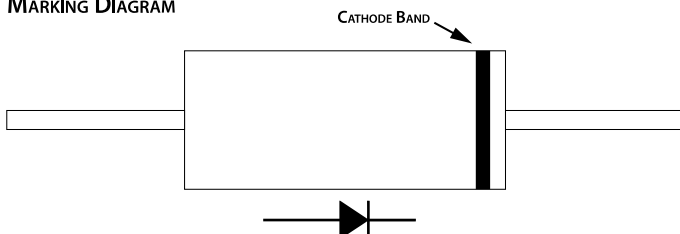
¹25°C ambient temperature unless stated otherwise.

Drawings

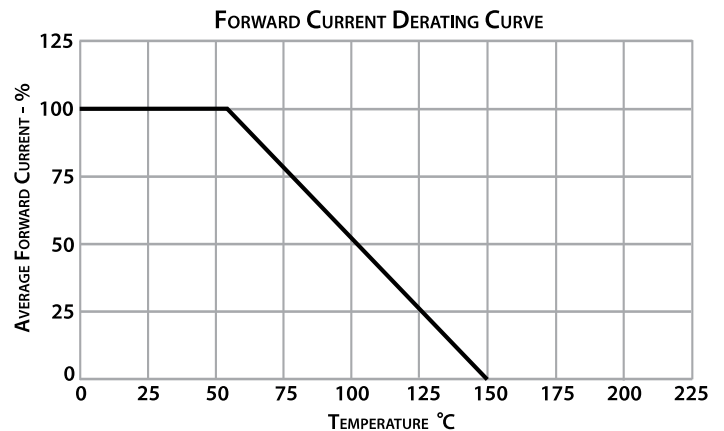


Dimensions in inches, tolerances ±0.020 except as noted.

MARKING DIAGRAM



MARKING TYPE: BLUE, INKJET
(MARKINGS WILL WRAP ENTIRE BODY OF DIODE AND ARE SUBJECT TO MINOR CHANGES)





Specification Definitions

	Specifications	Conditions
V_{RRM}	Maximum Repetitive Reverse Voltage	-
I_{FAVM}	Maximum Average Forward Current	At $T_A = 55^\circ\text{C}$
V_F	Maximum Forward Voltage Drop	At 20mA
I_R	Maximum Leakage Current	At V_{RRM}
I_{FSM}	Maximum Surge Current	At 8.3mS, Single Half Sine
C_J	Typical Junction Capacitance	At $V_R = 0\text{VDC}$, $f = 1\text{MHz}$
T_{RR}	Maximum Reverse Recovery Time	$I_F = 0.5 I_{FAVM}$; $I_R = -I_{FAVM}$; $I_{RR} = -0.25 I_{FAVM}$

Note: Specifications subject to change without notice. Photo is representation only.

